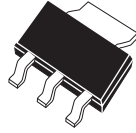


**CZTA27**  
**NPN HIGH VOLTAGE**  
**DARLINGTON TRANSISTOR**



**SOT-223 CASE**

# Central<sup>TM</sup>

**Semiconductor Corp.**

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CZTA27 type is a NPN Silicon Darlington Transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for applications requiring extremely high gain and high voltage.

**MARKING CODE: FULL PART NUMBER**

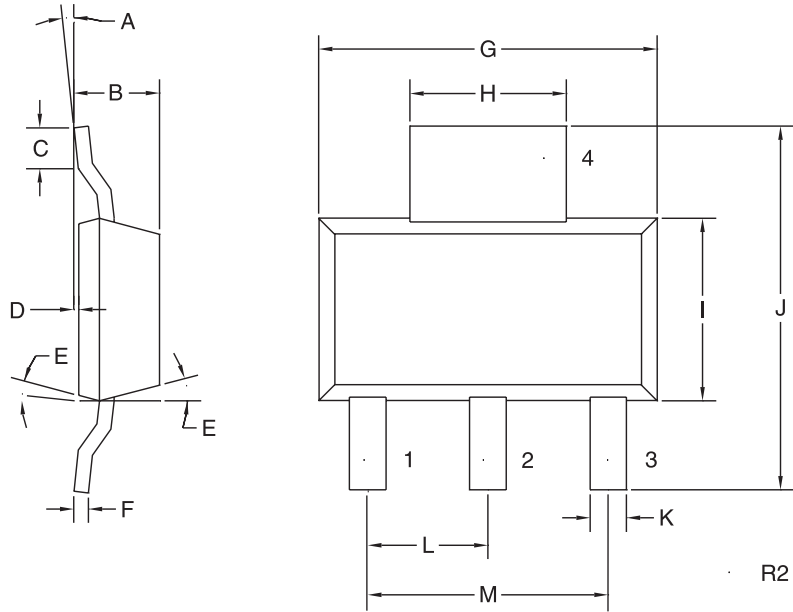
**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

	SYMBOL		UNITS
Collector-Emitter Voltage	$V_{CES}$	60	V
Emitter-Base Voltage	$V_{EBO}$	10	V
Continuous Collector Current	$I_C$	500	mA
Power Dissipation	$P_D$	2.0	W
Operating and Storage			
Junction Temperature	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$
Thermal Resistance	$\theta_{JA}$	62.5	$^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
$I_{CBO}$	$V_{CB}=50\text{V}$		100	nA
$I_{CES}$	$V_{CE}=50\text{V}$		500	nA
$I_{EBO}$	$V_{EB}=10\text{V}$		100	nA
$BV_{CBO}$	$I_C=100\mu\text{A}$	60		V
$BV_{CES}$	$I_C=100\mu\text{A}$	60		V
$V_{CE(SAT)}$	$I_C=100\text{mA}, I_B=0.1\text{mA}$		1.5	V
$V_{BE(ON)}$	$V_{CE}=5.0\text{V}, I_C=100\text{mA}$		2.0	V
$h_{FE}$	$V_{CE}=5.0\text{V}, I_C=10\text{mA}$	10,000		
$h_{FE}$	$V_{CE}=5.0\text{V}, I_C=100\text{mA}$	10,000		
$f_T$	$V_{CE}=5.0\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	125		MHz

**SOT-223 CASE - MECHANICAL OUTLINE**



**LEAD CODE:**

- 1) BASE
- 2) COLLECTOR
- 3) EMITTER
- 4) COLLECTOR

**MARKING CODE:**

**FULL PART NUMBER**

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0°	7°	0°	7°
B	0.063	0.067	1.60	1.70
C	0.022		0.55	
D	0.001	0.004	0.03	0.10
E	15°		15°	
F	0.009	0.013	0.23	0.33
G	0.248	0.264	6.30	6.71
H	0.114	0.122	2.90	3.10
I	0.130	0.146	3.30	3.71
J	0.264	0.287	6.71	7.29
K	0.024	0.031	0.61	0.79
L	0.091		2.31	
M	0.181		4.60	

SOT-223 (REV: R2)